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WHAT IS CLAIMED IS:

power buffered oxygen ash process.

9.

array.

	WHAT IS CALLED		
1	1: A method of fabricating an image sensor, comprising:		
2	forming a bottom antireflection coating over an exposed surface of an active		
3	image sensing device structure;		
4	forming a color filter array on the bottom antireflection coating; and		
5	substantially removing exposed portions of the bottom antireflection coating.		
1	2. The method of claim 1, wherein the bottom antireflection coating		
2	comprises a dyed organic film-forming material.		
1	3. The method of claim , wherein the bottom antireflection coating		
2	comprises a light-absorbing polymeric film-forming material.		
1	4. The method of claim 1, wherein the bottom antireflection coating has a		
2	thickness selected to improve an optical transmission characteristic of one or more		
3	colors of the color filter array.		
1	5. The method of claim 1, wherein the bottom antireflection coating is		
2	substantially transmissive to radiation in a wavelength range of about 400 nm to		
3	about 700 nm.		
1	6. The method of claim 1, wherein the color filter array comprises a		
2	plurality of colored photoresist structures.		
1	7. The method of claim 1, wherein exposed portions of the bottom		
2	antireflection coating are removed substantially by a plasma etch process.		
1	8. The method of claim 7, wherein the plasma etch process is a low-		

bottom antireflection coating at a substantially higher etch rate than the color filter

The method of claim 7, wherein the plasma etch process removes the

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1 2 3 4	10. a substantial device struct substantially	The method of claim 1, wherein the bottom antireflection coating forms by continuous layer over the exposed surface of the active image sensing the before exposed portions of the bottom antireflection coating are removed.
1 2 3		The method of claim 1, wherein the bottom antireflection coating forms barrier over metal structures at the exposed surface of the active image ce structure during formation of the color filter array.
1 2 3	12.	The method of claim 1, wherein the active image sensor device mprises a complementary metal-oxide-semiconductor (CMOS) image
,	School.	
1	13.	An image sensor system, comprising:
2	an ac	tive image sensing device structure;
3	a colo	or filter array; and

- an active image sensing device structure;
 a color filter array; and
 a bottom antireflection coating disposed between the color filter array and a
 surface of the active image sensing device structure.
- 14. The system of claim 13, wherein the bottom antireflection coating comprises a dyed organic film-forming material.
- 1 15. The system of claim 13, wherein the bottom antireflection coating comprises a light-absorbing polymeric film-forming material.
- 1 16. The system of claim 13, wherein the bottom antireflection coating has a 2 thickness selected to improve an optical transmission characteristic of one or more 3 colors of the color filter array.
- 1 17. The system of claim 13, wherein the bottom antireflection coating is 2 substantially transmissive to radiation in a wavelength range of about 400 nm to 3 about 700 nm.

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- The system of claim 13, wherein the color filter array comprises a 18. 1 plurality of colored photoresist structures. 2
- The system of claim 13, wherein the bottom antireflection coating has a 19. 1 substantially higher plasma etch rate than the color filter array. 2
 - The system of claim 13, wherein the active image sensor device 20. structure comprises a complementary metal-oxide-semiconductor (CMOS) image sensor.

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